

ABSTRACT

A field transistor for electrostatic discharge (ESD) protection and method for making such a transistor is described. The field transistor includes a gate conductive layer pattern formed on a field oxide layer. Since the gate conductive layer pattern is formed on the field oxide layer, a thin gate insulating layer having a high possibility of insulation breakdown is not used. To form an inversion layer for providing a current path between source and drain regions, a field oxide layer is interposed to form low concentration source and drain regions overlapped by the gate conductive layer pattern.